

EH2520TTS-9.216M TR



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD) 9.216MHz ± 20 ppm 0°C to +70°C

ELECTRICAL SPECIFICATIONS

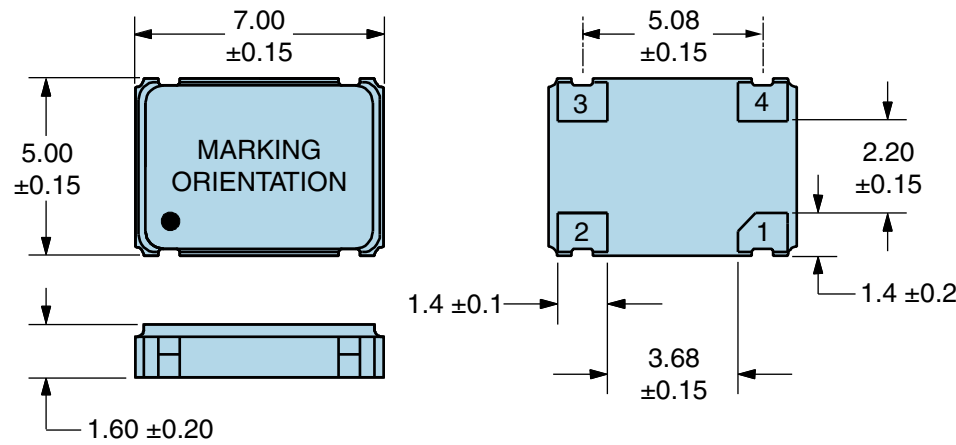
Nominal Frequency	9.216MHz
Frequency Tolerance/Stability	± 20 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ± 5 (%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 30 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

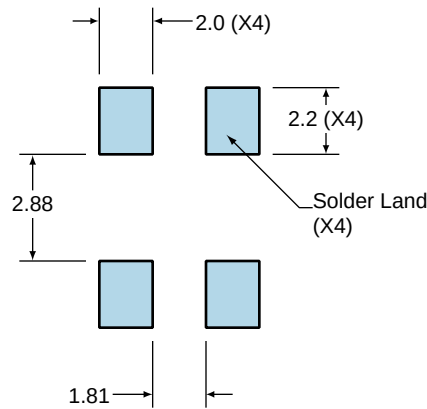


PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	9.2160M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

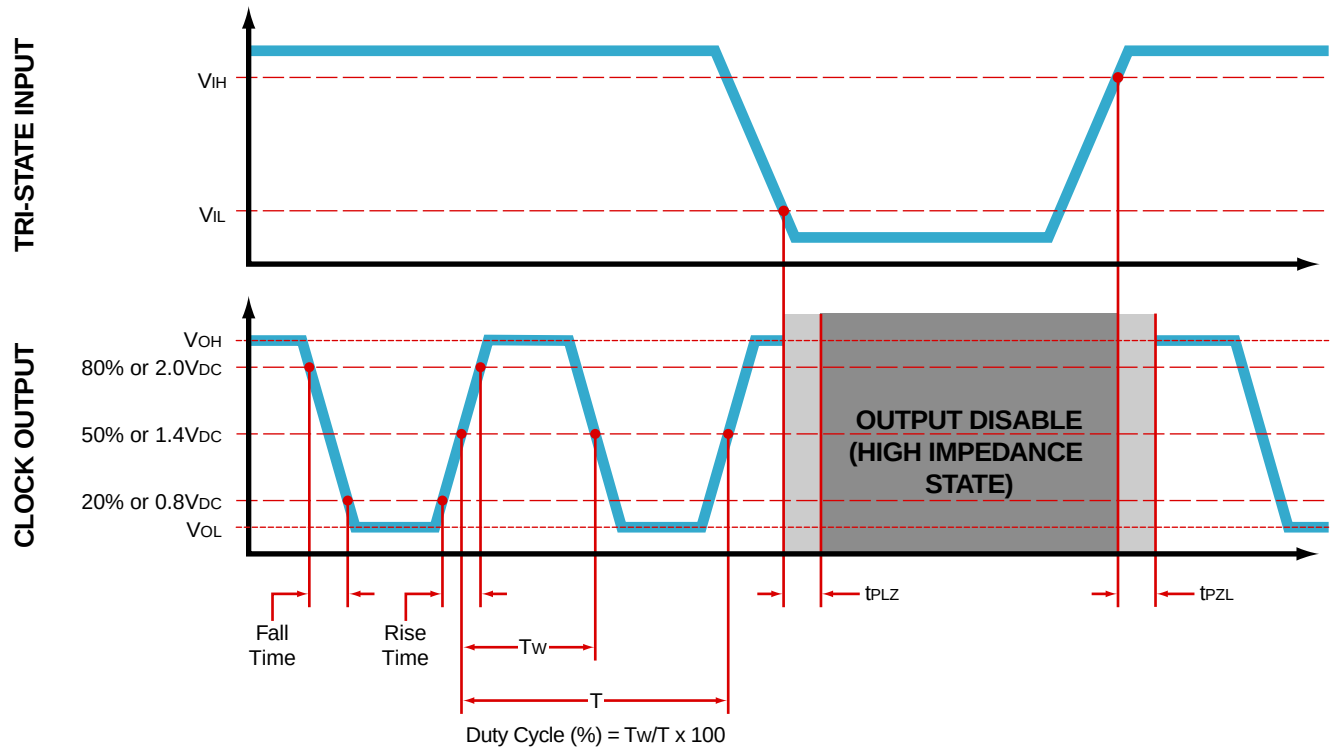
All Dimensions in Millimeters



All Tolerances are ±0.1

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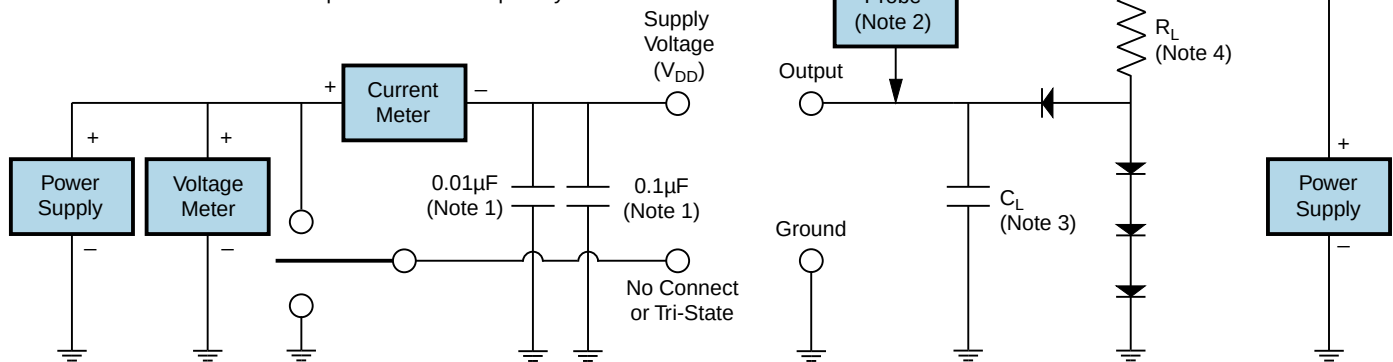
OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.1μF low frequency tantalum bypass capacitor in parallel with a 0.01μF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

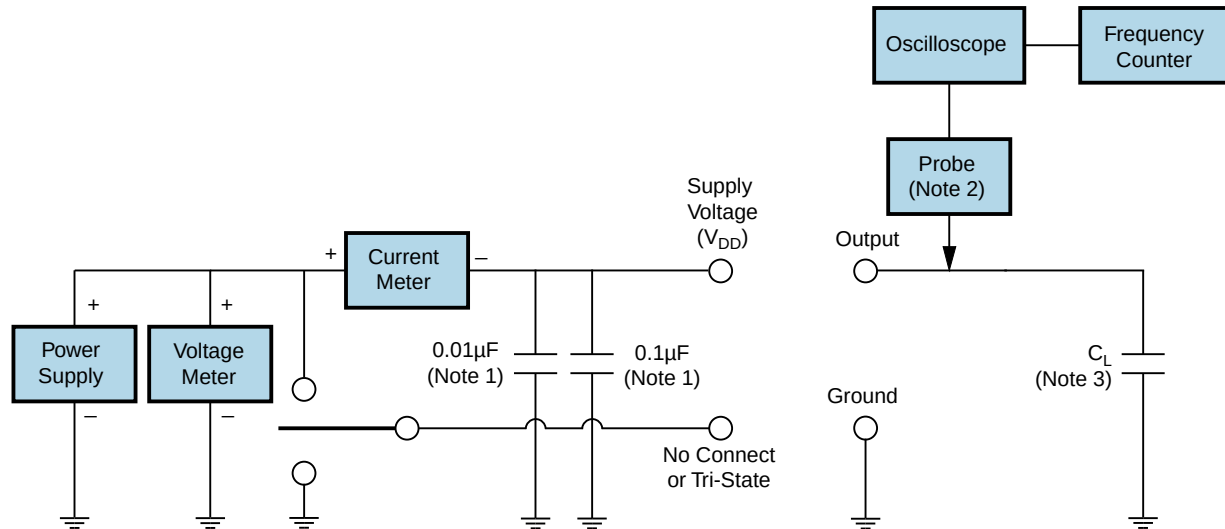
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

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Test Circuit for CMOS Output

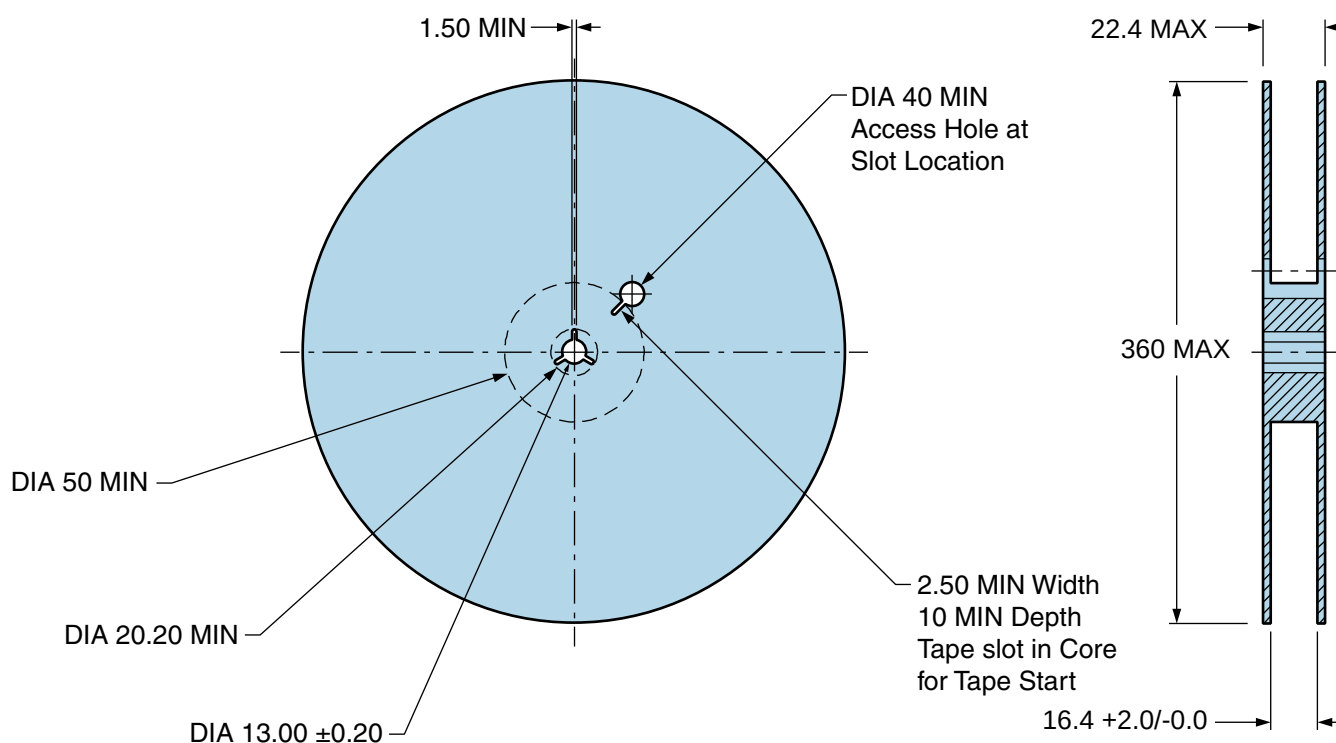


Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

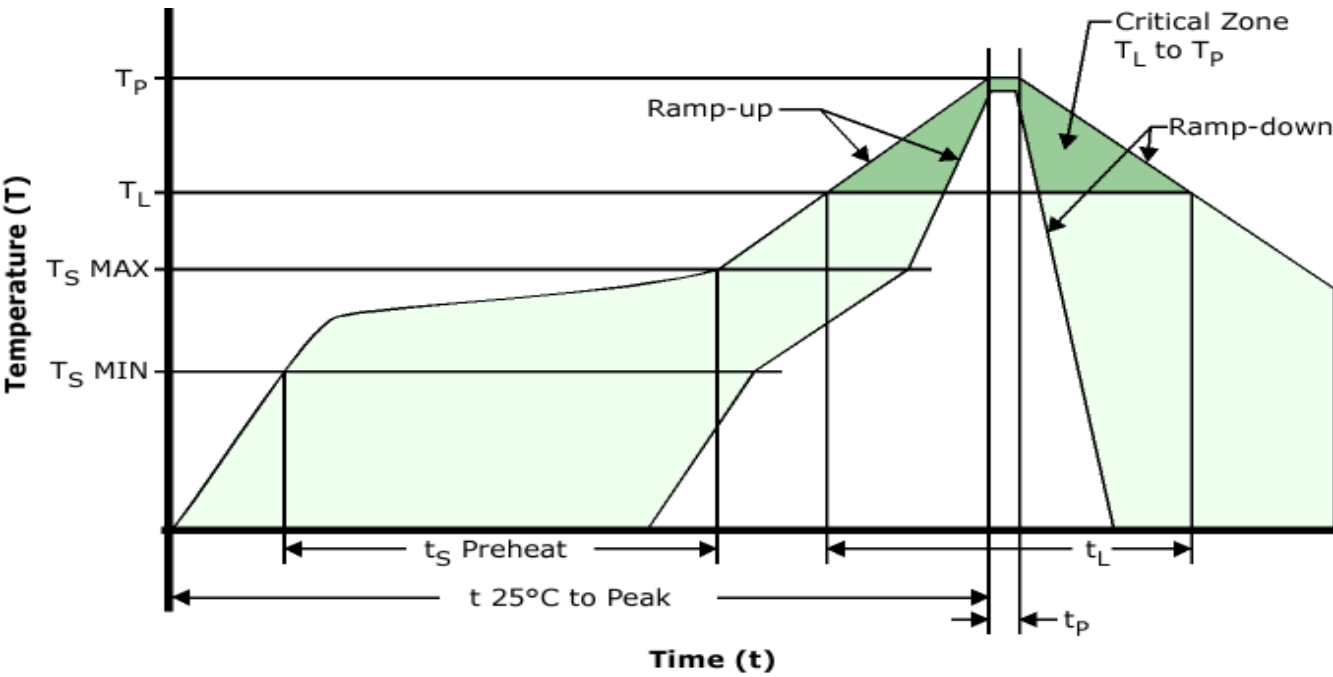
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Compliant to EIA-481



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Recommended Solder Reflow Methods

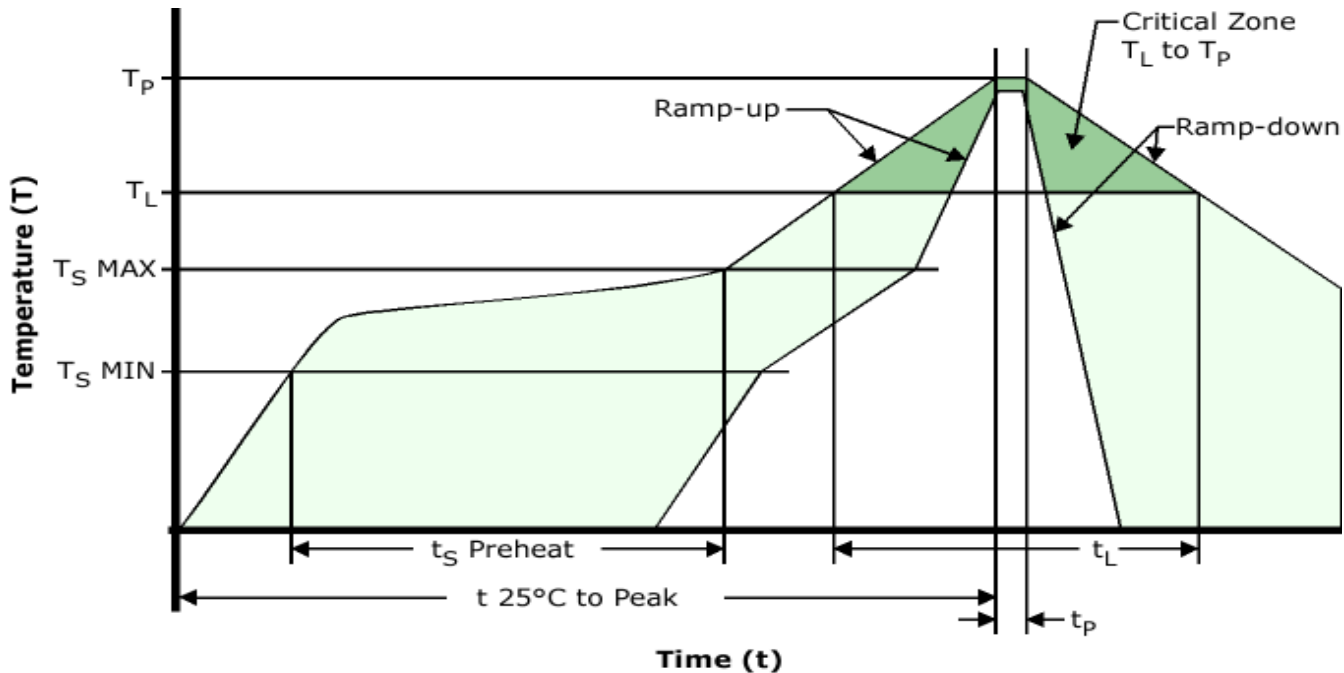


High Temperature Infrared/Convection

Ts MAX to Tl (Ramp-up Rate)	3°C/Second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	150°C
- Temperature Typical (Ts TYP)	175°C
- Temperature Maximum (Ts MAX)	200°C
- Time (ts MIN)	60 - 180 Seconds
Ramp-up Rate (Tl to Tp)	3°C/Second Maximum
Time Maintained Above:	
- Temperature (Tl)	217°C
- Time (tL)	60 - 150 Seconds
Peak Temperature (Tp)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (Tp Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 Seconds
Ramp-down Rate	6°C/Second Maximum
Time 25°C to Peak Temperature (t)	8 Minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

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Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T_S MAX to T_L (Ramp-up Rate) 5°C/Second Maximum

Preheat

- Temperature Minimum (T_S MIN) N/A
 - Temperature Typical (T_S TYP) 150°C
 - Temperature Maximum (T_S MAX) N/A
 - Time (t_s MIN) 60 - 120 Seconds

Ramp-up Rate (T_L to T_P) 5°C/Second Maximum

Time Maintained Above:

- Temperature (T_L) 150°C
 - Time (t_L) 200 Seconds Maximum

Peak Temperature (T_P) 240°C Maximum

Target Peak Temperature (T_P Target) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak (t_p) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Additional Notes Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)